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Epitaxial Ferromagnet on Ge(111): $\mathbf{Mn}_{5}\mathbf{Ge}_{3}$ MICHAEL HOCHSTRASSER, DANILO PESCIA, ETH Zurich, ROY WILLIS, The Pennsylvania State University, IVANA VOBORNIK, GIANCARLO PANACCIONE, GIOR-GIO ROSSI, TASC, INFM-CNR — Magnetic materials used for recording and reading information involve the use of the electron spin, while semiconducting devices normally take advantage of the electron charge. Recently, a big effort has been made in adding the spin degree of freedom to conventional semiconductors. A good potential candidate for spin injection in a silicon- compatible semiconductor are Mn₅Ge₃ thin films on Ge(111) [1]. To further gain information on the usefulness of possible spintronics applications of Mn₅Ge₃/Ge(111) multilayers angle resolved photoemission spectroscopy (ARPES) was employed to map the band dispersion of Mn_5Ge_3 films on Ge(111) above and below the Curie temperature. Furthermore, we performed temperature dependent x-ray magnetic dichroism measurements of Mn₅Ge₃ films on Ge(111) to probe the magnetic properties of Mn₅Ge₃. [1] C. Zeng et al., Appl. Phys. Lett. 83, 5002 (2003).

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